

UNISONIC TECHNOLOGIES CO., LTD

6NM70-S **Preliminary Power MOSFET**

6.0A, 700V N-CHANNEL **SUPER-JUNCTION MOSFET**

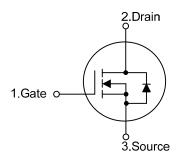
DESCRIPTION

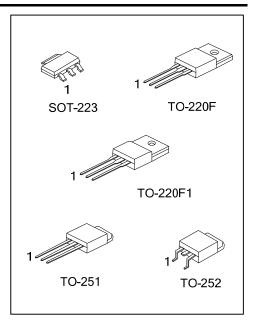
The UTC 6NM70-S is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

FEATURES

- * $R_{DS(on)}$ < 1.7 Ω @ V_{GS} =10V, I_{D} =3.0A
- * Improved dv/dt capability
- * Fast switching
- * 100% avalanche tested

SYMBOL

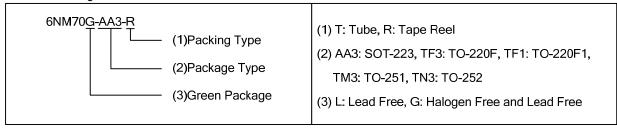




ORDERING INFORMATION

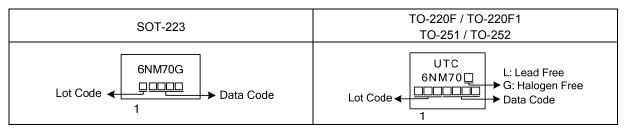
Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
-	6NM70G-AA3-R	SOT-223	G	D	S	Tape Reel	
6NM70L-TF1-T	6NM70G-TF1-T	TO-220F1	G	D	S	Tube	
6NM70L-TF3-T	6NM70G-TF3-T	TO-220F	G	D	S	Tube	
6NM70L-TM3-T	6NM70G-TM3-T	TO-251	G	D	S	Tube	
6NM70L-TN3-R	6NM70G-TN3-R	TO-252	G	D	S	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current		I _D	6.0	Α
Pulsed Drain Current (Note 2)		I _{DM}	24	Α
Single Pulsed Avalanche Energy (Note 3)		E _{AS}	132	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4	V/ns
Power Dissipation	SOT-223		5	W
	TO-220F/TO-220F1	P_{D}	40	W
	TO-251/TO-252		55	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 3. L = 120 mH, I_{AS} = 1.48A, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25 $^{\circ}$ C
- 4. $I_{SD} \le 6.0 \text{A}$, di/dt $\le 200 \text{A}/\mu \text{s}$, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25 ^{\circ}\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT	
Junction to Ambient	SOT-223		150	°C/W	
	TO-220F/TO-220F1	θ_{JA}	62.5		
	TO-251/TO-252		110		
Junction to Case	SOT-223		25		
	TO-220F/TO-220F1	θ_{JC}	3.13	°C/W	
	TO-251/TO-252		2.27		

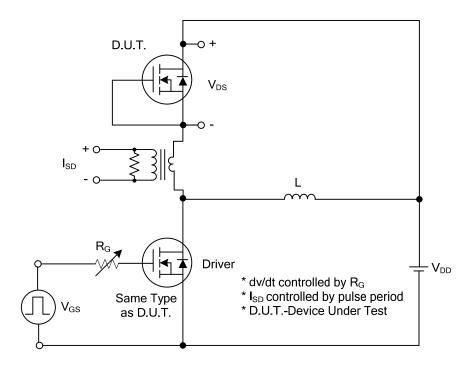
■ **ELECTRICAL CHARACTERISTICS** (T_C =25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV _{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	700			V		
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 700V, V_{GS} = 0V$			10	μA		
Cata Sauraa Laakaga Current	I _{GSS}	$V_{GS} = 30V, V_{DS} = 0V$			100	nA		
Gate-Source Leakage Current		$V_{GS} = -30V, V_{DS} = 0V$			-100	nA		
ON CHARACTERISTICS								
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.5		4.5	V		
Static Drain-Source On-State Resistance	R _{DS(ON)}	$V_{GS} = 10V, I_D = 3.0A$			1.7	Ω		
DYNAMIC CHARACTERISTICS								
Input Capacitance	C _{ISS}			260		pF		
Output Capacitance	Coss	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		120		pF		
Reverse Transfer Capacitance	C_{RSS}			17		pF		
SWITCHING CHARACTERISTICS								
Total Gate Charge (Note 1)	Q_G	V _{DS} =50V, I _D =1.3A, V _{GS} =10V 		35		nC		
Gate-Source Charge	Q_GS			1.8		nC		
Gate-Drain Charge	Q_GD			6.1		nC		
Turn-On Delay Time (Note 1)	t _{D(ON)}	V_{DD} =30V, I_{D} =0.5A, R_{G} =25 Ω		47.5		nS		
Turn-On Rise Time	t_R			60		nS		
Turn-Off Delay Time	t _{D(OFF)}	(Note 1,2)		96		nS		
Turn-Off Fall Time	t _F			48		nS		
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS								
Maximum Body-Diode Continuous Current	Is				6	Α		
Maximum Body-Diode Pulsed Current	I _{SM}				24	Α		
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	I _S =6.0A, V _{GS} =0V			1.4	V		
Reverse Recovery Time (Note 1)	t _{rr}	I _S =6.0A, V _{GS} =0V,		410		nS		
Reverse Recovery Charge	Q_{rr}	dI _F /dt=100A/μs		3		μC		

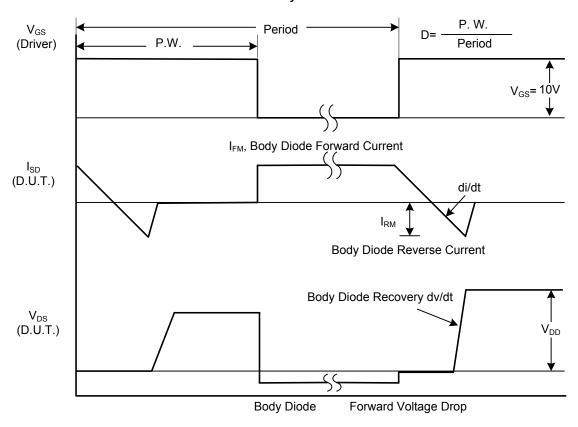
Notes: 1. Pulse Test : Pulse width \leq 300 μ s, Duty cycle \leq 2%.

^{2.} Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS

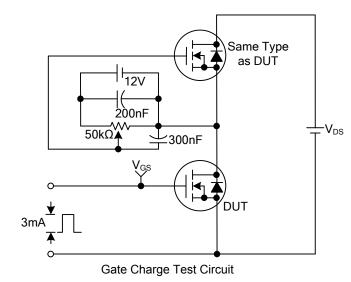


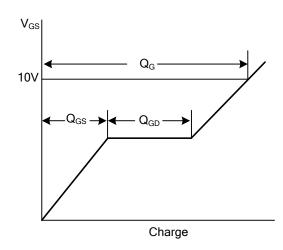
Peak Diode Recovery dv/dt Test Circuit



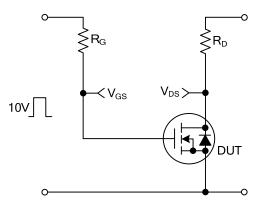
Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS (Cont.)

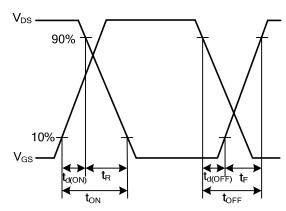




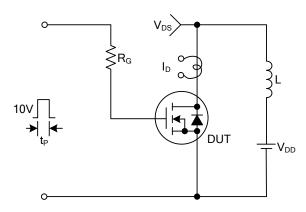
Gate Charge Waveforms



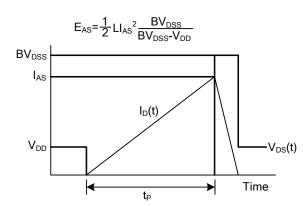
Resistive Switching Test Circuit



Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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